

#	Q	I	PT	P	Document ID	Issue Cat	Pages	Title	Current OP	Current XB	Retrieval	Inventor	C	C	2	3	4
5					US 20030228713	20031211	19	Methods of forming magnetoresistive memory	438/3			Nejad, Hasan et al.					
6					US 20030228711	20031211	19	METHODS OF FORMING MAGNETORESISTIVE MEMORY	438/3			Nejad, Hasan et al.					
7					US 20020155627	20021024	19	Method of fabricating magnetic random access	438/3	365/173		Okazawa, Takeshi et al.					
8					US 20020146851	20021010	21	Method of forming	438/3	257/E43.004		Okazawa, Takeshi et al.					
9					US 20020038681	20020404	11	Masking material for dry etching	148/421	148/422		Nakatani, Isao et al.					
10					US 6713802	20040330	11	Magnetic tunnel junction patterning usi	257/295	257/303;		Lee, Gill Yong					
11					US 6703249	20040309	19	Method of fabricating magnetic random access	438/4	257/295;		Okazawa, Takeshi et al.					
12					US 6629309	20030930	21	Mask-programmable ROM cell	716/16	365/185.14		Allen, III, Ernest					
13					US 6172902	20010109	13	Non-volatile magnetic random access memory	365/159	365/129;		Wegrove, Jean-Eric et al.					
14					US 5591652	19970107	43	Method of manufacturing flash memory with incli	438/259	257/E21.422		Matsushita, Tadashi					
15					US 5502321	19960326	33	Flash memory having inclined channel	257/316	257/317;		Matsushita, Tadashi					

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